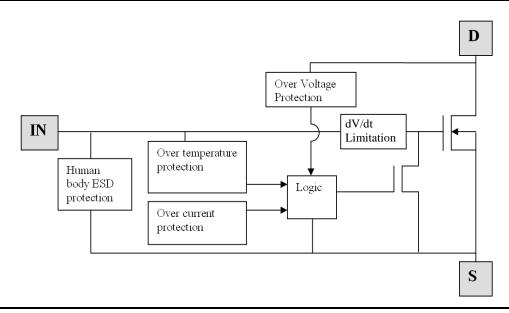


# **Functional Block Diagram**



# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for Short Circuit Protection	V <sub>DS(SC)</sub>	24	V
Continuous Input Voltage	V <sub>IN</sub>	-0.5 to +6	V
Continuous Input Current @-0.2V $\leq$ V <sub>IN</sub> $\leq$ 6V Continuous Input Current @V <sub>IN</sub> $<$ -0.2V or V <sub>IN</sub> $>$ 6V	lin	No limit   I <sub>IN</sub>   ≤2	mA
Pulsed Drain Current @V <sub>IN</sub> = 3.3V	I <sub>DM</sub>	5	Α
Pulsed Drain Current @V <sub>IN</sub> = 5V	I <sub>DM</sub>	6	Α
Continuous Source Current (Body Diode) (Note 5)	Is	2.5	Α
Pulsed Source Current (Body Diode)	I <sub>SM</sub>	10	Α
Unclamped Single Pulse Inductive Energy, T <sub>J</sub> = +25°C, I <sub>D</sub> = 0.5A, V <sub>DD</sub> = 24V	E <sub>AS</sub>	480	mJ
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4000	V
Charged Device Model	V <sub>CDM</sub>	1000	V

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T <sub>A</sub> = +25°C (Note 5) Linear Derating Factor	P <sub>D</sub>	1.0 8.0	W mW/°C
Power Dissipation at T <sub>A</sub> = +25°C (Note 6) Linear Derating Factor	P <sub>D</sub>	1.6 12.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	125	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	83	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	39	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

Notes:

<sup>5.</sup> For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.

<sup>6.</sup> For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.

<sup>7.</sup> Thermal resistance between junction and the mounting surfaces of drain and source pins.

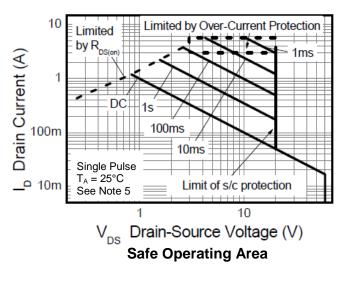


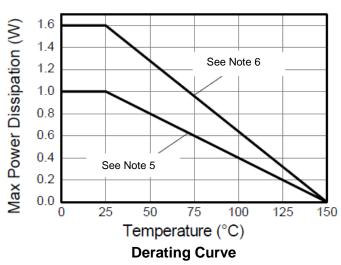
### **Recommended Operating Conditions**

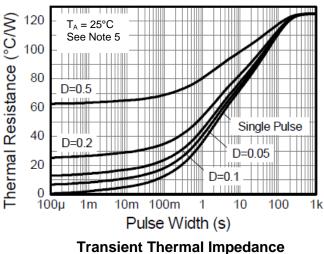
The ZXMS6005SG is optimized for use with  $\mu C$  operating from 3.3V and 5V supplies.

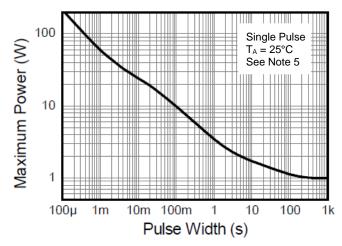
Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V <sub>IN</sub>	0	5.5	V
Ambient Temperature Range	T <sub>A</sub>	-40	+125	°C
High Level Input Voltage for MOSFET to be on	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V <sub>IL</sub>	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	$V_P$	0	24	V

### **Thermal Characteristics**









**Pulse Power Dissipation** 



# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise stated.)

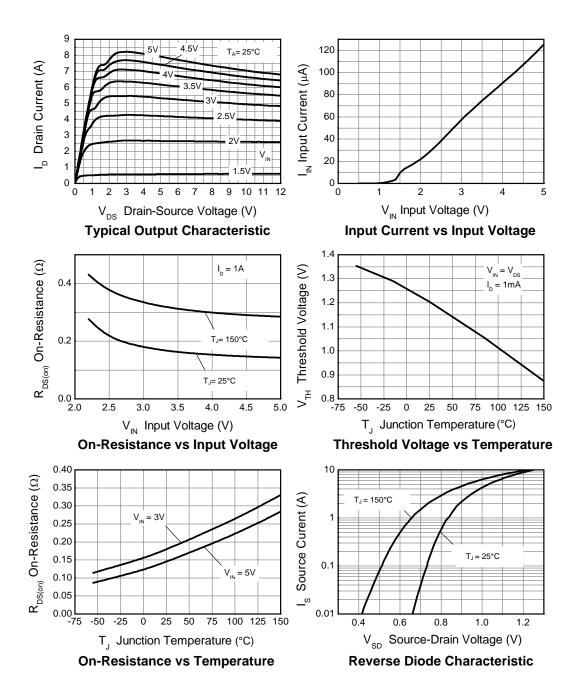
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	65	70	V	$I_D = 10mA$
Off State Drain Current		_	_	1	μA	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V
	I <sub>DSS</sub>	_	_	2		$V_{DS} = 36V$ , $V_{IN} = 0V$
Input Threshold Voltage	V <sub>IN(TH)</sub>	0.7	1.2	1.5	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$
Input Current	l	1	60	100	μΑ	$V_{IN} = 3V$
Input Current	I <sub>IN</sub>	_	120	200		V <sub>IN</sub> = 5V
Input Current While Over Temperature Active	_	_	_	300	μA	V <sub>IN</sub> = 5V
Static Drain-Source On-State Resistance	_	_	170	250	mΩ	$V_{IN} = 3V, I_D = 1A$
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	_	150	200		$V_{IN} = 5V, I_D = 1A$
Continuous Drain Current (Note 5)	- I <sub>D</sub>	1.4	_	_		V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C
		1.6	_	_	А	V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C
Continuous Drain Current (Note 6)		1.9	_	_		V <sub>IN</sub> = 3V, T <sub>A</sub> = +25°C
		2.0	_	_		V <sub>IN</sub> = 5V, T <sub>A</sub> = +25°C
Our ( ) ( ) ( ) ( ) ( ) ( ) ( )	I <sub>D(LIM)</sub>	2.2	5	_	А	V <sub>IN</sub> = 3V
Current Limit (Note 8)		3.3	7	_		V <sub>IN</sub> = 5V
Dynamic Characteristics						
Turn On Delay Time	t <sub>D(ON)</sub>	-	6	_		$V_{DD} = 12V$ , $I_D = 1A$ , $V_{GS} = 5V$
Rise Time	t <sub>R</sub>	1	14	_	μs	
Turn Off Delay Time	t <sub>D(OFF)</sub>	1	34	_		
Fall Time	t <sub>F</sub>	1	19	_		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 9)	T <sub>JT</sub>	+150	+175	_	°C	_
Thermal Hysteresis (Note 9)	_	_	+10	_	°C	_

Notes: 8. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

<sup>9.</sup> Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

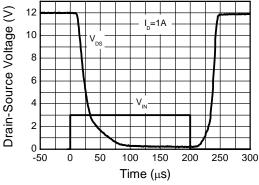


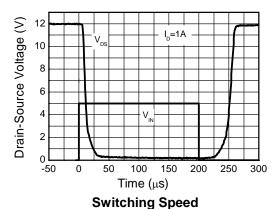
# **Typical Characteristics**



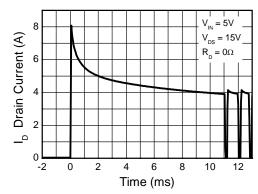


# **Typical Characteristics** (Cont.)





# **Switching Speed**



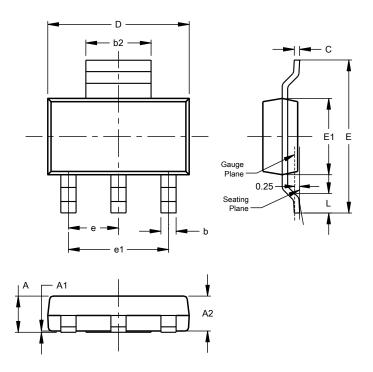
**Typical Short Circuit Protection** 



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

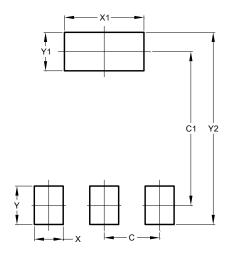


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α	-	1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
Е	6.70	7.30		
E1	3.30	3.70		
е	-		2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

July 2018



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